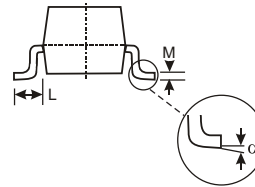
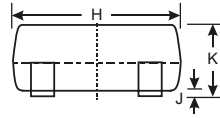
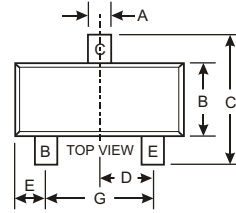
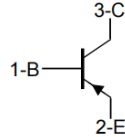
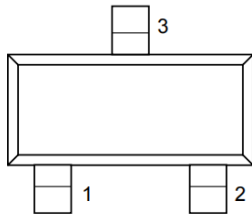


Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT5551)
- Ideal for Low Power Amplification and Switching
- Marking Code:2L



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	-150	V
Collector-Base Voltage	V _{CBO}	-160	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mAdc

• THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) TA=25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance,Junction to Ambient	R _{ΘJA}	556	°C/W
Total Device Dissipation Alumina Substrate,(2) TA=25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance,Junction to Ambient	R _{ΘJA}	417	°C/W
Junction and Storage Temperature	T _j , T _{stg}	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage ($I_C = -1.0\text{mA}, I_B = 0$)	$V_{(BR)CEO}$	-150	-	-	V
Collector-Base Breakdown voltage ($I_C = -100\mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	-160	-	-	V
Emitter-Base Breakdown Voltage ($I_E = -10\mu\text{A}, I_C = 0$)	$V_{(BR)EBO}$	-5	-	-	V
Collector Cutoff Current ($V_{CB} = -120\text{V}, I_E = 0$) ($V_{CB} = -120\text{V}, I_E = 0, T_A = 100^\circ\text{C}$)	I_{CBO}	- -	- -	-50 -50	nA μA

ON CHARACTERISTICS

DC Current Gain ($I_C = -1.0\text{mA}, V_{CE} = -5.0\text{V}$) ($I_C = -10\text{mA}, V_{CE} = -5.0\text{V}$) ($I_C = -50\text{mA}, V_{CE} = -5.0\text{V}$)	HFE	50 80 50	- - -	- 250 -	
Collector-Emitter Saturation Voltage ($I_C = -10\text{mA}, I_B = -1.0\text{mA}$) ($I_C = -50\text{mA}, I_B = -5.0\text{mA}$)	$V_{CE(S)}$	- -	- -	-0.2 -0.5	V
Base-Emitter Saturation Voltage ($I_C = -10\text{mA}, I_B = -1.0\text{mA}$) ($I_C = -50\text{mA}, I_B = -5.0\text{mA}$)	$V_{BE(S)}$	- -	- -	-1 -1	V

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = -10\text{mA}, V_{CE} = -10\text{V}, f = 100\text{MHz}$)	fT	100	-	300	MHz
Output Capacitance ($V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$)	Cobo	-	-	6	PF
Small-Signal Current Gain ($I_C = -1.0\text{mA}, V_{CE} = -10\text{V}, f = 1.0\text{kHz}$)	hfe	40	-	200	
Noise Figure ($I_C = -200\mu\text{A}, V_{CE} = -5.0\text{V}, R_s = 10\Omega, f = 1.0\text{kHz}$)	NF	-	-	8	dB

TYPICAL TRANSIENT CHARACTERISTICS

